Zibo Seno Electronic Engineering Co., Ltd.



SB3040PT – SB30200PT 🕲



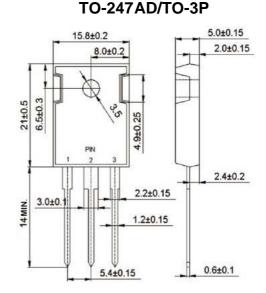
30.0A SCHOTTKY BARRIER DIODE

Features

- Schottky Barrier Chip
- Ideally Suited for Automatic Assembly
- Low Power Loss, High Efficiency
- For Use in Low Voltage Application
- Guard Ring Die Construction
- Plastic Case Material has UL Flammability Classification Rating 94V-O

Mechanical Data

- Case: TO-247AD/TO-3P, Molded Plastic
- Terminals: Plated Leads Solderable per
- MIL-STD-202, Method 208
 Polarity: See Diagram
- Mounting Position: Any
- Lead Free: For RoHS / Lead Free Version



Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	SB 3040 PT	SB 3045 PT	SB 3050 PT	SB 3060 PT	SB 30100 PT	SB 30150 PT	SB 30200 PT	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vr	40	45	50	60	100	150	200	V
RMS Reverse Voltage	VR(RMS)	28	31	35	42	70	105	140	V
Average Rectified Output Current $@T_L = 75^{\circ}C$ (Note 1)	lo	30							А
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	275						A	
Forward Voltage $@I_F = 15A$	Vfm	0.70		0.75		0.80	0.90		V
Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 100^{\circ}C$	Iгм	0.2 20							mA
Typical Junction Capacitance (Note 2)	Cj	350		2	30		200		pF
Typical Thermal Resistance (Note 1)	R∂JA	3.0 2.0				°C/W			
Operating and Storage Temperature Range	Тj, Tsтg	-55 to +150							°C

Note: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case.

2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

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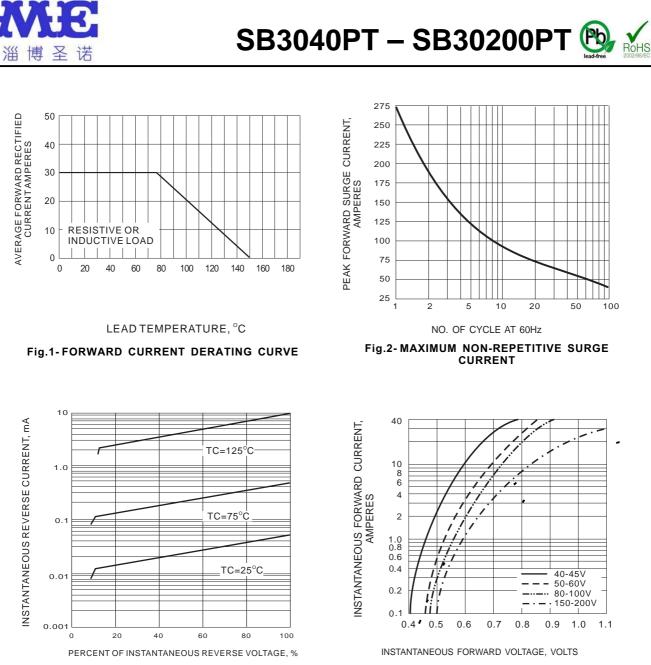


Fig.3- TYPICAL REVERSE CHARACTERISTIC

Fig.4- TYPICAL INSTANTANEOUS FORWARD CHARACTERISTIC